

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 25.00MM×19.0MM OUTLINE
- ✧ DUAL DIGIT
- ✧ SINGLE COLOT
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

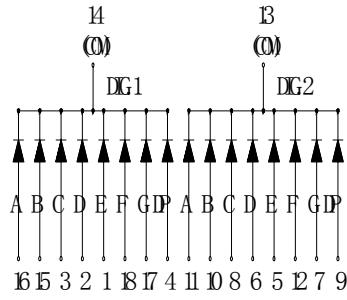
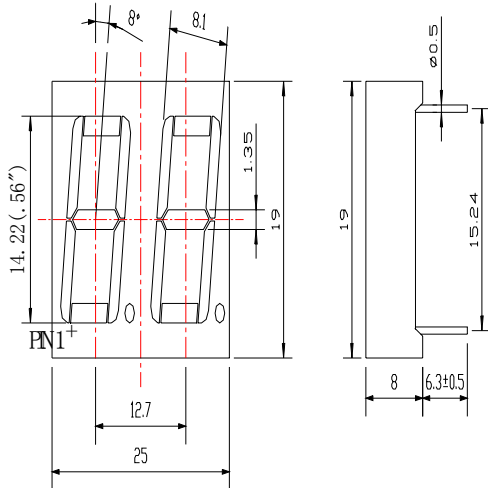
The REC-S5261ASR/CSR is a 0.56 inches (14.20mm) digit height, 12.6mm×19.0mm outline, single color, dual digit numeric display. This display utilizes red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and red segments.

DEVICE

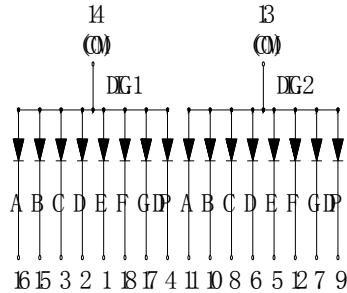
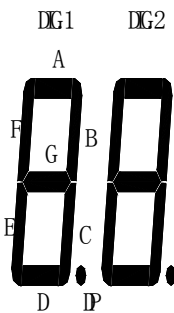
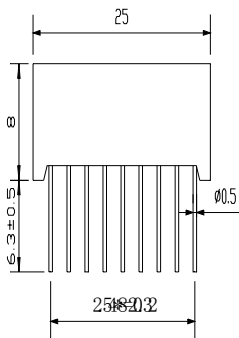
PART NO.	EMITTING COLOR	DESCRIPTION
REC-S5261ASR/CSR	Super-Red	Black Face & Red Segments

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PACKAGE DIMENSION



- | | |
|-----------|----------------|
| 1DG1A0EE | 10DG2A0EB |
| 2DG1A0ED | 11DG2A0EA |
| 3DG1A0EC | 12DG2A0EF |
| 4DG1A0EIP | 13DG2COMNCAHDE |
| 5DG2A0EE | 14DG1COMNCAHDE |
| 6DG2A0ED | 15DG1A0EB |
| 7DG2A0EG | 16DG1A0EA |
| 8DG2A0EC | 17DG1A0EG |
| 9DG2A0EIP | 18DG1A0EF |



- | | |
|-------------|----------------|
| 1DG1CAH0EE | 10DG2CAH0EB |
| 2DG1CAH0ED | 11DG2CAH0EA |
| 3DG1CAH0EC | 12DG2CAH0EF |
| 4DG1CAH0EIP | 13DG2COMNCAHDE |
| 5DG2CAH0EE | 14DG1COMNCAHDE |
| 6DG2CAH0ED | 15DG1CAH0EB |
| 7DG2CAH0EG | 16DG1CAH0EA |
| 8DG2CAH0EC | 17DG1CAH0EG |
| 9DG2CAH0EIP | 18DG1CAH0EF |

ABSOLUTE MAXIMUM RATING AT $T_A=25^\circ\text{C}$

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	60	mW
Peak Forward Current per Seg.	I_{PF}	80	mA
Continuous Forward Current per Seg.	I_{AF}	20	mA
Reverse Voltage per Seg.	V_R	5	V
Operating Temperature Range, T_{opr}		- 25° C to + 60° C	
Storage Temperature Range, T_{stg}		- 30° C to + 85° C	

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Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C

ELECTRO – OPTICAL CHARACTERISTICS AT T_A=25° C

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I _V (I _F =20mA)	mcd	7	13	15
Peak Emission Wavelength, λ _p (I _F =20mA)	nm		645	
Special Line Half-Width, Δλ (I _F =20mA)	nm		30	
Forward Voltage per Seg., V _F (I _F =20mA)	V	1.8	2.15	2.50
Reverse Current per chipSeg., I _R , (V _R =5V)	μA			100
Luminous Intensity Matching Ratio, I _{V-m} (I _F =20mA)				2 :1